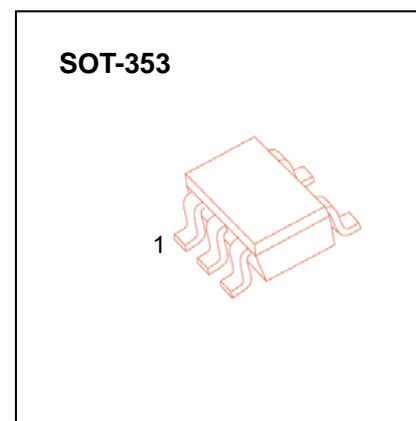


## General purpose transistors (dual transistors)

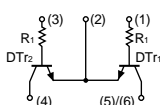


### FEATURES

- Two DTC143T chips in a package
- Mounting possible with SOT-353 automatic mounting machines.
- Transistor elements are independent, eliminating interference.
- Mounting cost and area be cut in half.

**Marking: G3**

Equivalent circuit



### Absolute maximum ratings (Ta=25°C)

Symbol	Parameter	LIMITS	Unit
V <sub>CBO</sub>	Collector-Base Voltage	50	V
V <sub>CEO</sub>	Collector-Emitter Voltage	50	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current -Continuous	100	mA
P <sub>C</sub>	Collector Dissipation	150	mW
T <sub>j</sub>	Junction temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~+150	°C

### ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =50μA, I <sub>E</sub> =0	50			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =1mA, I <sub>B</sub> =0	50			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =50μA, I <sub>C</sub> =0	5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =50V, I <sub>E</sub> =0			0.5	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =4V, I <sub>C</sub> =0			0.5	μA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =1mA	100		600	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =5mA, I <sub>B</sub> =0.25mA			0.3	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =10V, I <sub>E</sub> =-5mA, f=100MHz		250		MHz
Input resistor	R <sub>1</sub>		3.29	4.7	6.11	kΩ